Cheol Seong Hwang

List of Publications by Citations

611 papers	27,155 citations	77 h-index	142 g-index
634 ext. papers	30,256 ext. citations	5.9 avg, IF	7.17 L-index

#	Paper	IF	Citations
611	Atomic structure of conducting nanofilaments in TiO2 resistive switching memory. *Nature Nanotechnology*, **2010**, 5, 148-53	28.7	1672
610	Multifunctional wearable devices for diagnosis and therapy of movement disorders. *Nature Nanotechnology*, **2014**, 9, 397-404	28.7	1037
609	Resistive switching mechanism of TiO2 thin films grown by atomic-layer deposition. *Journal of Applied Physics*, **2005**, 98, 033715	2.5	938
608	Emerging memories: resistive switching mechanisms and current status. *Reports on Progress in Physics*, **2012**, 75, 076502	14.4	733
607	Ferroelectricity and antiferroelectricity of doped thin HfO2-based films. *Advanced Materials*, **2015**, 27, 1811-31	24	554
606	Nanofilamentary resistive switching in binary oxide system; a review on the present status and outlook. *Nanotechnology*, **2011**, 22, 254002	3.4	463
605	Efficient CH3 NH3 PbI3 Perovskite Solar Cells Employing Nanostructured p-Type NiO Electrode Formed by a Pulsed Laser Deposition. *Advanced Materials*, **2015**, 27, 4013-9	24	414
604	Evolution of phases and ferroelectric properties of thin Hf0.5Zr0.5O2 films according to the thickness and annealing temperature. *Applied Physics Letters*, **2013**, 102, 242905	3.4	352
603	A resistive memory in semiconducting BiFeO□thin-film capacitors. *Advanced Materials*, **2011**, 23, 1277-81	24	348
602	Anode-interface localized filamentary mechanism in resistive switching of TiO2 thin films. *Applied Physics Letters*, **2007**, 91, 012907	3.4	348
601	Resistive switching materials for information processing. *Nature Reviews Materials*, **2020**, 5, 173-195	73.3	318
600	Identification of a determining parameter for resistive switching of TiO2 thin films. *Applied Physics Letters*, **2005**, 86, 262907	3.4	296
599	High dielectric constant TiO2 thin films on a Ru electrode grown at 250 °C by atomic-layer deposition. *Applied Physics Letters*, **2004**, 85, 4112-4114	3.4	280
598	Deposition of extremely thin (Ba,Sr)TiO3 thin films for ultra-large-scale integrated dynamic random access memory application. *Applied Physics Letters*, **1995**, 67, 2819-2821	3.4	261
597	A Review of Three-Dimensional Resistive Switching Cross-Bar Array Memories from the Integration and Materials Property Points of View. *Advanced Functional Materials*, **2014**, 24, 5316-5339	15.6	259
596	Al-Doped TiO2 Films with Ultralow Leakage Currents for Next Generation DRAM Capacitors. *Advanced Materials*, **2008**, 20, 1429-1435	24	248
595	Effect of high-pressure oxygen annealing on negative bias illumination stress-induced instability of InGaZnO thin film transistors. *Applied Physics Letters*, **2011**, 98, 103509	3.4	231

594	Thin HfxZr1-xO2 Films: A New Lead-Free System for Electrostatic Supercapacitors with Large Energy Storage Density and Robust Thermal Stability. *Advanced Energy Materials*, **2014**, 4, 1400610	21.8	221
593	Review and perspective on ferroelectric HfO2-based thin films for memory applications. *MRS Communications*, **2018**, 8, 795-808	2.7	209
592	Localized switching mechanism in resistive switching of atomic-layer-deposited TiO2 thin films. *Applied Physics Letters*, **2007**, 90, 242906	3.4	198
591	First-principles study on doping and phase stability of HfO2. *Physical Review B*, **2008**, 78,	3.3	193
590	The effects of crystallographic orientation and strain of thin Hf0.5Zr0.5O2 film on its ferroelectricity. *Applied Physics Letters*, **2014**, 104, 072901	3.4	191
589	First-principles study of point defects in rutile TiO2−x. *Physical Review B*, **2006**, 73,	3.3	189
588	Memristors for Energy-Efficient New Computing Paradigms. *Advanced Electronic Materials*, **2016**, 2, 1600090	6.2	188
587	An artificial nociceptor based on a diffusive memristor. *Nature Communications*, **2018**, 9, 417	17.4	183
586	Origin of Subthreshold Swing Improvement in Amorphous Indium Gallium Zinc Oxide Transistors. *Electrochemical and Solid-State Letters*, **2008**, 11, H157		177
585	Surface and grain boundary energy as the key enabler of ferroelectricity in nanoscale hafnia-zirconia: a comparison of model and experiment. *Nanoscale*, **2017**, 9, 9973-9986	7.7	162
584	Capacitors with an Equivalent Oxide Thickness of . *Advanced Functional Materials*, **2010**, 20, 2989-3003	15.6	160
583	Bioresorbable Electronic Stent Integrated with Therapeutic Nanoparticles for Endovascular Diseases. *ACS Nano*, **2015**, 9, 5937-46	16.7	158
582	Highly Uniform, Electroforming-Free, and Self-Rectifying Resistive Memory in the Pt/Ta2O5/HfO2-x/TiN Structure. *Advanced Functional Materials*, **2014**, 24, 5086-5095	15.6	157
581	A comparative study on the electrical conduction mechanisms of (Ba0.5Sr0.5)TiO3 thin films on Pt and IrO2 electrodes. *Journal of Applied Physics*, **1998**, 83, 3703-3713	2.5	155
580	A study on the wake-up effect of ferroelectric Hf0.5Zr0.5O2 films by pulse-switching measurement. *Nanoscale*, **2016**, 8, 1383-9	7.7	153
579	Highly improved uniformity in the resistive switching parameters of TiO2 thin films by inserting Ru nanodots. *Advanced Materials*, **2013**, 25, 1987-92	24	152
578	Toward a multifunctional monolithic device based on pyroelectricity and the electrocaloric effect of thin antiferroelectric Hf x Zr 1− O 2 films. *Nano Energy*, **2015**, 12, 131-140	17.1	144
577	A detailed understanding of the electronic bipolar resistance switching behavior in Pt/TiO2/Pt structure. *Nanotechnology*, **2011**, 22, 254010	3.4	140

576	The conical shape filament growth model in unipolar resistance switching of TiO2 thin film. *Applied Physics Letters*, **2009**, 94, 122109	3.4	137
575	32 □2 Crossbar Array Resistive Memory Composed of a Stacked Schottky Diode and Unipolar Resistive Memory. *Advanced Functional Materials*, **2013**, 23, 1440-1449	15.6	136
574	Improved Ferroelectric Switching Endurance of La-Doped HfZrO Thin Films. *ACS Applied Materials & Interfaces*, **2018**, 10, 2701-2708	9.5	134
573	Pt/Ta2 O5 /HfO2- x /Ti resistive switching memory competing with multilevel NAND flash. *Advanced Materials*, **2015**, 27, 3811-6	24	134
572	Grain size engineering for ferroelectric Hf0.5Zr0.5O2 films by an insertion of Al2O3 interlayer. *Applied Physics Letters*, **2014**, 105, 192903	3.4	134
571	Effect of Zr Content on the Wake-Up Effect in Hf1-xZrxO2 Films. *ACS Applied Materials & Interfaces*, **2016**, 8, 15466-75	9.5	132
570	Low-Power, Self-Rectifying, and Forming-Free Memristor with an Asymmetric Programing Voltage for a High-Density Crossbar Application. *Nano Letters*, **2016**, 16, 6724-6732	11.5	131
569	Temporary formation of highly conducting domain walls for non-destructive read-out of ferroelectric domain-wall resistance switching memories. *Nature Materials*, **2018**, 17, 49-56	27	131
568	Thickness-dependent dielectric constants of (Ba,Sr)TiO3 thin films with Pt or conducting oxide electrodes. *Journal of Applied Physics*, **2002**, 92, 432-437	2.5	128
567	Depletion layer thickness and Schottky type carrier injection at the interface between Pt electrodes and (Ba, Sr)TiO3 thin films. *Journal of Applied Physics*, **1999**, 85, 287-295	2.5	127
566	Low Temperature (. *Journal of the Electrochemical Society*, **2006**, 153, F69	3.9	126
565	Comparison between ZnO films grown by atomic layer deposition using H2O or O3 as oxidant. *Thin Solid Films*, **2005**, 478, 103-108	2.2	125
564	Nonvolatile Memory Materials for Neuromorphic Intelligent Machines. *Advanced Materials*, **2018**, 30, e1704729	24	121
563	Effect of forming gas annealing on the ferroelectric properties of Hf0.5Zr0.5O2 thin films with and without Pt electrodes. *Applied Physics Letters*, **2013**, 102, 112914	3.4	117
562	Ferroelectricity in undoped-HfO2 thin films induced by deposition temperature control during atomic layer deposition. *Journal of Materials Chemistry C*, **2016**, 4, 6864-6872	7.1	116
561	Dielectric and electrical properties of sputter grown (Ba,Sr)TiO3 thin films. *Journal of Applied Physics*, **1999**, 86, 506-513	2.5	116
560	A Pt/TiO(2)/Ti Schottky-type selection diode for alleviating the sneak current in resistance switching memory arrays. *Nanotechnology*, **2010**, 21, 195201	3.4	113
559	Prospective of Semiconductor Memory Devices: from Memory System to Materials. *Advanced Electronic Materials*, **2015**, 1, 1400056	6.4	108

558	(Ba,Sr)TiO3 thin films for ultra large scale dynamic random access memory.. *Materials Science and Engineering B: Solid-State Materials for Advanced Technology*, **1998**, 56, 178-190	3.1	108
557	Novel high-□dielectrics for next-generation electronic devices screened by automated ab initio calculations. *NPG Asia Materials*, **2015**, 7, e190-e190	10.3	106
556	Electrically configurable electroforming and bipolar resistive switching in Pt/TiO2/Pt structures. *Nanotechnology*, **2010**, 21, 305203	3.4	104
555	Influences of interfacial intrinsic low-dielectric layers on the dielectric properties of sputtered (Ba,Sr)TiO3 thin films. *Applied Physics Letters*, **2000**, 77, 124-126	3.4	104
554	Understanding the formation of the metastable ferroelectric phase in hafnia-zirconia solid solution thin films. *Nanoscale*, **2018**, 10, 716-725	7.7	103
553	Ferroelectric properties and switching endurance of Hf0.5Zr0.5O2 films on TiN bottom and TiN or RuO2 top electrodes. *Physica Status Solidi - Rapid Research Letters*, **2014**, 8, 532-535	2.5	102
552	Metal oxide memories based on thermochemical and valence change mechanisms. *MRS Bulletin*, **2012**, 37, 131-137	3.2	102
551	Enhanced electrical properties of SrTiO3 thin films grown by atomic layer deposition at high temperature for dynamic random access memory applications. *Applied Physics Letters*, **2008**, 92, 222903	3.4	102
550	Resistive Switching in Pt□Al[sub 2]O[sub 3]□TiO[sub 2]□Ru Stacked Structures. *Electrochemical and Solid-State Letters*, **2006**, 9, G343		102
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547	Study on the degradation mechanism of the ferroelectric properties of thin Hf0.5Zr0.5O2 films on TiN and Ir electrodes. *Applied Physics Letters*, **2014**, 105, 072902	3.4	99
546	Comparison of HfO2 films grown by atomic layer deposition using HfCl4 and H2O or O3 as the oxidant. *Journal of Applied Physics*, **2003**, 94, 3641-3647	2.5	98
545	Atomic Layer Deposition of SrTiO3 Thin Films with Highly Enhanced Growth Rate for Ultrahigh Density Capacitors. *Chemistry of Materials*, **2011**, 23, 2227-2236	9.6	96
544	Resistive switching memory: observations with scanning probe microscopy. *Nanoscale*, **2011**, 3, 490-502	7.7	96
543	Self-Limited Switching in Ta2O5/TaOx Memristors Exhibiting Uniform Multilevel Changes in Resistance. *Advanced Functional Materials*, **2015**, 25, 1527-1534	15.6	93
542	Study on the resistive switching time of TiO2 thin films. *Applied Physics Letters*, **2006**, 89, 012906	3.4	93
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540	Giant Negative Electrocaloric Effects of Hf Zr O Thin Films. *Advanced Materials*, **2016**, 28, 7956-7961	24	91
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538	Atomic Layer Deposition of Ru Thin Films Using 2,4-(Dimethylpentadienyl)(ethylcyclopentadienyl)Ru by a Liquid Injection System. *Journal of the Electrochemical Society*, **2007**, 154, D95	3.9	83
537	Densification and Mechanical Properties of Titanium Diboride with Silicon Nitride as a Sintering Aid. *Journal of the American Ceramic Society*, **2004**, 82, 3037-3042	3.8	83
536	Thermal annealing effects on the structural and electrical properties of HfO2/Al2O3 gate dielectric stacks grown by atomic layer deposition on Si substrates. *Journal of Applied Physics*, **2003**, 94, 2563-2571	2.5	81
535	Deposition and Electrical Characterization of Very ThinSrTiO3Films for Ultra Large Scale Integrated Dynamic Random Access Memory Application. *Japanese Journal of Applied Physics*, **1995**, 34, 5178-5183	1.4	77
534	Suppression in the negative bias illumination instability of Zn-Sn-O transistor using oxygen plasma treatment. *Applied Physics Letters*, **2011**, 99, 102103	3.4	76
533	Comparison between atomic-layer-deposited HfO2 films using O3 or H2O oxidant and Hf[N(CH3)2]4 precursor. *Applied Physics Letters*, **2004**, 85, 5953-5955	3.4	72
532	Tunneling-assisted Poole-Frenkel conduction mechanism in HfO2 thin films. *Journal of Applied Physics*, **2005**, 98, 113701	2.5	72
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530	Thermodynamic and Kinetic Origins of Ferroelectricity in Fluorite Structure Oxides. *Advanced Electronic Materials*, **2019**, 5, 1800522	6.4	71
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527	Improvement of the photo-bias stability of the ZnSnO field effect transistors by an ozone treatment. *Journal of Materials Chemistry*, **2012**, 22, 10994		67
526	Study on the electrical conduction mechanism of bipolar resistive switching TiO2 thin films using impedance spectroscopy. *Applied Physics Letters*, **2010**, 96, 152909	3.4	67
525	Investigation on the Growth Initiation of Ru Thin Films by Atomic Layer Deposition. *Chemistry of Materials*, **2010**, 22, 2850-2856	9.6	65
524	Chemically Conformal ALD of SrTiO[sub 3] Thin Films Using Conventional Metallorganic Precursors. *Journal of the Electrochemical Society*, **2005**, 152, C229	3.9	65
523	Stabilization of Tetragonal HfO2 under Low Active Oxygen Source Environment in Atomic Layer Deposition. *Chemistry of Materials*, **2012**, 24, 3534-3543	9.6	64

522	Real-time identification of the evolution of conducting nano-filaments in TiO2 thin film ReRAM. *Scientific Reports*, **2013**, 3, 3443	4.9	64
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520	Electronic resistance switching in the Al/TiO(x)/Al structure for forming-free and area-scalable memory. *Nanoscale*, **2015**, 7, 11063-74	7.7	63
519	Local structure and conduction mechanism in amorphous InGaZnO films. *Applied Physics Letters*, **2009**, 94, 112112	3.4	63
518	Atomic-layer-deposited Al2O3 thin films with thin SiO2 layers grown by in situ O3 oxidation. *Journal of Applied Physics*, **2004**, 96, 2323-2329	2.5	63
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516	Study on the internal field and conduction mechanism of atomic layer deposited ferroelectric Hf0.5Zr0.5O2 thin films. *Journal of Materials Chemistry C*, **2015**, 3, 6291-6300	7.1	62
515	Memristive tri-stable resistive switching at ruptured conducting filaments of a Pt/TiO/Pt cell. *Nanotechnology*, **2012**, 23, 185202	3.4	62
514	Growth Behavior of Al-Doped TiO2 Thin Films by Atomic Layer Deposition. *Chemistry of Materials*, **2008**, 20, 3723-3727	9.6	62
513	Transformation of the Crystalline Structure of an ALD TiO[sub 2] Film on a Ru Electrode by O[sub 3] Pretreatment. *Electrochemical and Solid-State Letters*, **2006**, 9, F5		62
512	Influence of carrier injection on resistive switching of TiO2 thin films with Pt electrodes. *Applied Physics Letters*, **2006**, 89, 162912	3.4	62
511	Atomic Layer Deposition of SrTiO3 Films with Cyclopentadienyl-Based Precursors for Metal/Insulator/Metal Capacitors. *Chemistry of Materials*, **2013**, 25, 953-961	9.6	61
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509	Growth Characteristics of Atomic Layer Deposited TiO[sub 2] Thin Films on Ru and Si Electrodes for Memory Capacitor Applications. *Journal of the Electrochemical Society*, **2005**, 152, C552	3.9	60
508	Scale-up and optimization of HfO2-ZrO2 solid solution thin films for the electrostatic supercapacitors. *Nano Energy*, **2017**, 39, 390-399	17.1	59
507	Leakage current of sol-gel derived Pb(Zr, Ti)O3 thin films having Pt electrodes. *Applied Physics Letters*, **1999**, 75, 3411-3413	3.4	59
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498	Role of ZrO2 incorporation in the suppression of negative bias illumination-induced instability in ZnSnO thin film transistors. *Applied Physics Letters*, **2011**, 98, 122110	3.4	53
497	Cyclic PECVD of Ge[sub 2]Sb[sub 2]Te[sub 5] Films Using Metallorganic Sources. *Journal of the Electrochemical Society*, **2007**, 154, H318	3.9	53
496	Correlation of the change in transfer characteristics with the interfacial trap densities of amorphous InGaZnO thin film transistors under light illumination. *Applied Physics Letters*, **2011**, 98, 232102	3.4	52
495	Reduction of Electrical Defects in Atomic Layer Deposited HfO2 Films by Al Doping. *Chemistry of Materials*, **2010**, 22, 4175-4184	9.6	52
494	High-k properties of atomic-layer-deposited HfO2 films using a nitrogen-containing Hf[N(CH3)2]4 precursor and H2O oxidant. *Applied Physics Letters*, **2003**, 83, 5503-5505	3.4	51
493	Review of defect chemistry in fluorite-structure ferroelectrics for future electronic devices. *Journal of Materials Chemistry C*, **2020**, 8, 10526-10550	7.1	50
492	Influence of the oxygen concentration of atomic-layer-deposited HfO2 films on the dielectric property and interface trap density. *Applied Physics Letters*, **2005**, 86, 112907	3.4	50
491	Sub-Picosecond Processes of Ferroelectric Domain Switching from Field and Temperature Experiments. *Advanced Functional Materials*, **2012**, 22, 192-199	15.6	49
490	Synthesis of SnS Thin Films by Atomic Layer Deposition at Low Temperatures. *Chemistry of Materials*, **2017**, 29, 8100-8110	9.6	49
489	Atomic Layer Deposition and Electrical Properties of SrTiO[sub 3] Thin Films Grown Using Sr(C[sub 11]H[sub 19]O[sub 2])[sub 2], Ti(Oi-C[sub 3]H[sub 7])[sub 4], and H[sub 2]O. *Journal of the Electrochemical Society*, **2007**, 154, G127	3.9	49
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487	Ferroelectric properties of lightly doped La:HfO2 thin films grown by plasma-assisted atomic layer deposition. *Applied Physics Letters*, **2017**, 111, 132903	3.4	48

486	Epitaxial Brownmillerite Oxide Thin Films for Reliable Switching Memory. *ACS Applied Materials & Interfaces*, **2016**, 8, 7902-11	9.5	48
485	Structure and electrical properties of Al-doped HfO2 and ZrO2 films grown via atomic layer deposition on Mo electrodes. *ACS Applied Materials & Interfaces*, **2014**, 6, 22474-82	9.5	48
484	Chemical Vapor Deposition of Ru Thin Films with an Enhanced Morphology, Thermal Stability, and Electrical Properties Using a RuO4 Precursor. *Chemistry of Materials*, **2009**, 21, 207-209	9.6	48
483	Preparation and Electrical Properties ofSrTiO3Thin Films Deposited by Liquid Source Metal-Organic Chemical Vapor Deposition (MOCVD). *Japanese Journal of Applied Physics*, **1996**, 35, 4890-4895	1.4	48
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480	Thickness effect of ultra-thin Ta2O5 resistance switching layer in 28 nm-diameter memory cell. *Scientific Reports*, **2015**, 5, 15965	4.9	47
479	Structural properties and electronic structure of HfO2-ZrO2 composite films. *Physical Review B*, **2010**, 82,	3.3	47
478	Improvement in the leakage current characteristic of metal-insulator-metal capacitor by adopting RuO2 film as bottom electrode. *Applied Physics Letters*, **2011**, 99, 022901	3.4	47
477	Influence of Substrates on the Nucleation and Growth Behaviors of Ge2Sb2Te5 Films by Combined Plasma-Enhanced Atomic Layer and Chemical Vapor Deposition. *Chemistry of Materials*, **2009**, 21, 2386-2396	9.6	47
476	Atomic Layer Deposition of Al2O3 Thin Films from a 1-Methoxy-2-methyl-2-propoxide Complex of Aluminum and Water. *Chemistry of Materials*, **2005**, 17, 626-631	9.6	47
475	Post-Annealing Effects on Fixed Charge and Slow/Fast Interface States of TiN/Al2O3/p-Si Metal–Oxide–Semiconductor Capacitor. *Japanese Journal of Applied Physics*, **2003**, 42, 1222-1226	1.4	47
474	Orientation effects in chemical solution derived Pb(Zr0.3,Ti0.7)O3 thin films on ferroelectric properties. *Thin Solid Films*, **2002**, 416, 264-270	2.2	47
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472	ZnO nanoparticle growth on single-walled carbon nanotubes by atomic layer deposition and a consequent lifetime elongation of nanotube field emission. *Applied Physics Letters*, **2007**, 90, 263104	3.4	46
471	Effects of carbon residue in atomic layer deposited HfO2 films on their time-dependent dielectric breakdown reliability. *Applied Physics Letters*, **2007**, 90, 182907	3.4	46
470	Plasma-Enhanced Atomic Layer Deposition of TiO[sub 2] and Al-Doped TiO[sub 2] Films Using N[sub 2]O and O[sub 2] Reactants. *Journal of the Electrochemical Society*, **2009**, 156, G138	3.9	45
469	Impact of O3 feeding time on TiO2 films grown by atomic layer deposition for memory capacitor applications. *Journal of Applied Physics*, **2007**, 102, 024109	2.5	45

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467	Highly Flexible Resistive Switching Memory Based on the Electronic Switching Mechanism in the Al/TiO/Al/Polyimide Structure. *ACS Applied Materials & Interfaces*, **2018**, 10, 1828-1835	9.5	44
466	Understanding the Coexistence of Two Bipolar Resistive Switching Modes with Opposite Polarity in Pt/TiO/Ti/Pt Nanosized ReRAM Devices. *ACS Applied Materials & Interfaces*, **2018**, 10, 29766-29778	9.5	44
465	Properties of lanthanum oxide thin films deposited by cyclic chemical vapor deposition using tris(isopropyl-cyclopentadienyl)lanthanum precursor. *Journal of Applied Physics*, **2006**, 100, 024111	2.5	44
464	Voltage Drop in a Ferroelectric Single Layer Capacitor by Retarded Domain Nucleation. *Nano Letters*, **2017**, 17, 7796-7802	11.5	43
463	Influences of metal, non-metal precursors, and substrates on atomic layer deposition processes for the growth of selected functional electronic materials. *Coordination Chemistry Reviews*, **2013**, 257, 3154-3176	23.2	43
462	Role of Ru nano-dots embedded in TiO2 thin films for improving the resistive switching behavior. *Applied Physics Letters*, **2010**, 97, 232904	3.4	43
461	In Situ Control of Oxygen Vacancies in TaO Thin Films via Plasma-Enhanced Atomic Layer Deposition for Resistive Switching Memory Applications. *ACS Applied Materials & Interfaces*, **2017**, 9, 13286-13292	9.5	42
460	Ferroelectric domain wall memory with embedded selector realized in LiNbO single crystals integrated on Si wafers. *Nature Materials*, **2020**, 19, 1188-1194	27	42
459	Conformal Formation of (GeTe2)(1⊠)(Sb2Te3)x Layers by Atomic Layer Deposition for Nanoscale Phase Change Memories. *Chemistry of Materials*, **2012**, 24, 2099-2110	9.6	42
458	Improvements in Growth Behavior of CVD Ru Films on Film Substrates for Memory Capacitor Integration. *Journal of the Electrochemical Society*, **2005**, 152, C15	3.9	42
457	A comprehensive study on the mechanism of ferroelectric phase formation in hafnia-zirconia nanolaminates and superlattices. *Applied Physics Reviews*, **2019**, 6, 041403	17.3	41
456	Improvement in Photo-Bias Stability of High-Mobility Indium Zinc Oxide Thin-Film Transistors by Oxygen High-Pressure Annealing. *IEEE Electron Device Letters*, **2013**, 34, 894-896	4.4	41
455	Identification of the controlling parameter for the set-state resistance of a TiO2 resistive switching cell. *Applied Physics Letters*, **2010**, 96, 112904	3.4	41
454	Threshold switching in Si-As-Te thin film for the selector device of crossbar resistive memory. *Applied Physics Letters*, **2012**, 100, 123505	3.4	41
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450	Fabrication of high-quality single-crystal Cu thin films using radio-frequency sputtering. *Scientific Reports*, **2014**, 4, 6230	4.9	38
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